

General Description

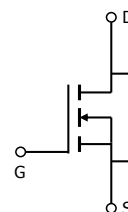
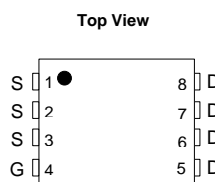
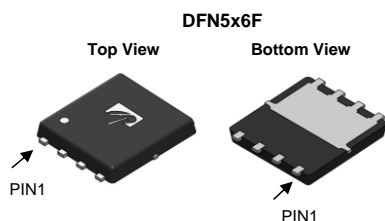
- Proprietary α MOS5™ technology
- Low $R_{DS(ON)}$
- Optimized switching parameters for better EMI performance
- Enhanced body diode for robustness and fast reverse recovery

Applications

- SMPS with PFC, Flyback and LLC topologies
- Silver ATX, adapter, TV, lighting, Server power

Product Summary

$V_{DS} @ T_{j,max}$	700V
I_{DM}	44A
$R_{DS(ON),max}$	< 0.42 Ω
$Q_{g,typ}$	20nC
$E_{oss} @ 400V$	2.6 μ J

 100% UIS Tested
 100% R_g Tested


Orderable Part Number	Package Type	Form	Minimum Order Quantity
AONS420A60	DFN5x6F	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 20	V
Gate-Source Voltage (dynamic) AC ($f > 1\text{Hz}$)	V_{GS}	± 30	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	11	A
	$T_C=100^\circ\text{C}$	8.3	
Pulsed Drain Current ^C	I_{DM}	44	
Continuous Drain Current	$T_A=25^\circ\text{C}$	2.2	A
	$T_A=70^\circ\text{C}$	1.8	
Avalanche Current ^C	I_{AR}	2.5	A
Repetitive avalanche energy ^C	E_{AR}	3.1	mJ
Single pulsed avalanche energy ^G ($T_J=25^\circ\text{C}$, $V_{GS}=10\text{V}$, $I_L=2\text{A}$, $L=105\text{mH}$, $R_{GS}=25\Omega$)	E_{AS}	210	mJ
MOSFET dv/dt ruggedness	dv/dt	100	V/ns
Diode reverse recovery	dv/dt	20	V/ns
$V_{DS}=0$ to 400V , $I_F \leq 10\text{A}$, $T_J=25^\circ\text{C}$	di/dt	100	A/us
Power Dissipation ^B	$T_C=25^\circ\text{C}$	156	W
	Derate above 25°C	1.3	W/ $^\circ\text{C}$
Power Dissipation ^A	$T_A=25^\circ\text{C}$	4.2	W
	$T_A=70^\circ\text{C}$	2.7	W/ $^\circ\text{C}$
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	25	30	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A,D}		Steady-State	45	55
Maximum Junction-to-Case	$R_{\theta JC}$	0.5	0.8	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V, T _J =25°C	600			V
		I _D =250μA, V _{GS} =0V, T _J =150°C		700		
BV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D =250μA, V _{GS} =0V		0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600V, V _{GS} =0V			1	μA
		V _{DS} =480V, T _J =125°C			10	
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =5V, I _D =250μA		3.2		V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =5.5A		0.38	0.42	Ω
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =5.5A		10		S
V _{SD}	Diode Forward Voltage	I _S =5.5A, V _{GS} =0V		0.86	1.2	V
I _S	Maximum Body-Diode Continuous Current				11	A
I _{SM}	Maximum Body-Diode Pulsed Current ^C				44	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =100V, f=1MHz		955		pF
C _{oss}	Output Capacitance			29		pF
C _{o(er)}	Effective output capacitance, energy related ^I	V _{GS} =0V, V _{DS} =0 to 480V, f=1MHz		30		pF
C _{o(tr)}	Effective output capacitance, time related ^J			122		pF
C _{rss}	Reverse Transfer Capacitance	V _{GS} =0V, V _{DS} =100V, f=1MHz		2.4		pF
R _g	Gate resistance	f=1MHz		4.8		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =480V, I _D =5.5A		20		nC
Q _{gs}	Gate Source Charge			4.6		nC
Q _{gd}	Gate Drain Charge			6.6		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =400V, I _D =5.5A, R _G =5Ω		20		ns
t _r	Turn-On Rise Time			13		ns
t _{D(off)}	Turn-Off DelayTime			43		ns
t _f	Turn-Off Fall Time			16		ns
t _{rr}	Body Diode Reverse Recovery Time			251		ns
I _{rm}	Peak Reverse Recovery Current	I _F =5.5A, di/dt=100A/μs, V _{DS} =400V		19		A
Q _{rr}	Body Diode Reverse Recovery Charge			3.1		μC

A. The value of R_{θJA} is measured with the device in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} t_s ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. L=60mH, I_{AS}=1A, R_G=25Ω, Starting T_J=25°C.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

I. C_{o(er)} is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}.

J. C_{o(tr)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

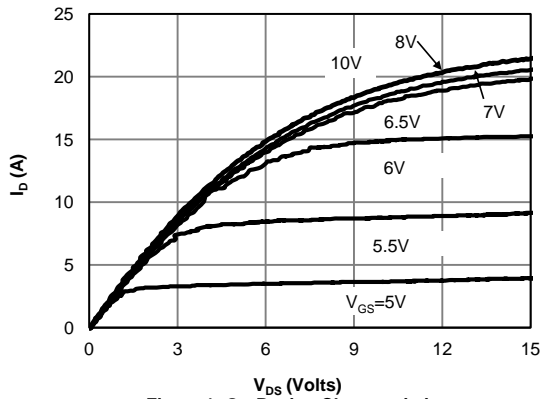


Figure 1: On-Region Characteristics

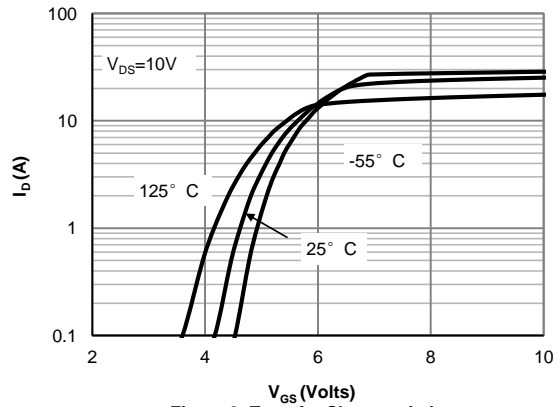


Figure 2: Transfer Characteristics

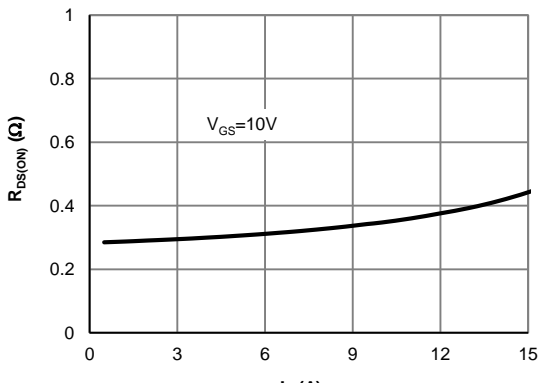


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

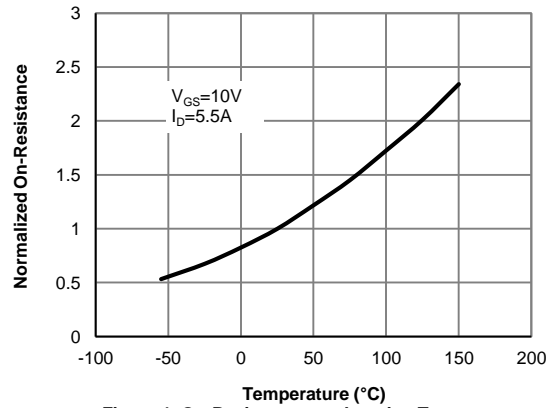


Figure 4: On-Resistance vs. Junction Temperature

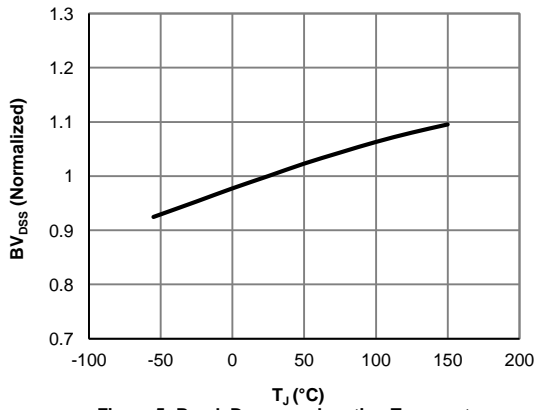


Figure 5: Break Down vs. Junction Temperature

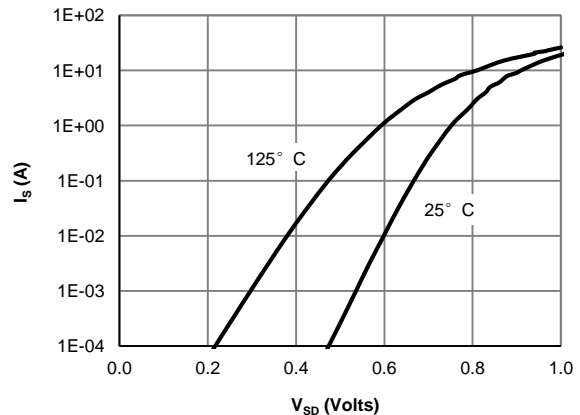


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

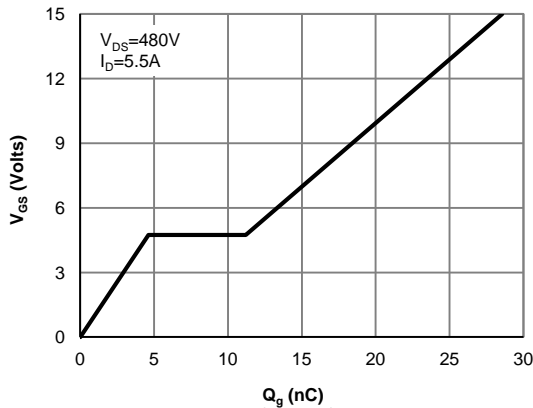


Figure 7: Gate-Charge Characteristics

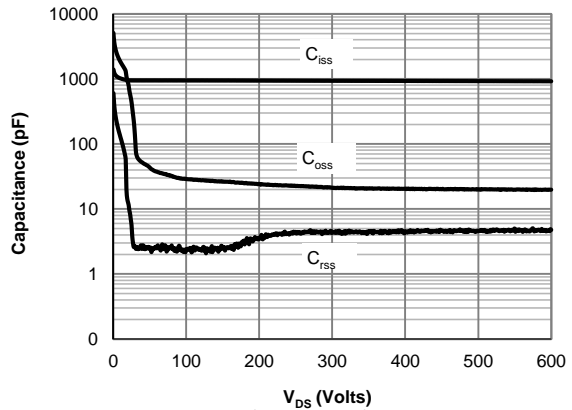


Figure 8: Capacitance Characteristics

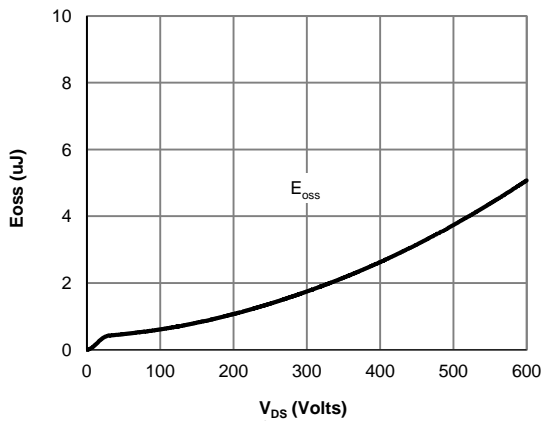


Figure 9: Coss stored Energy

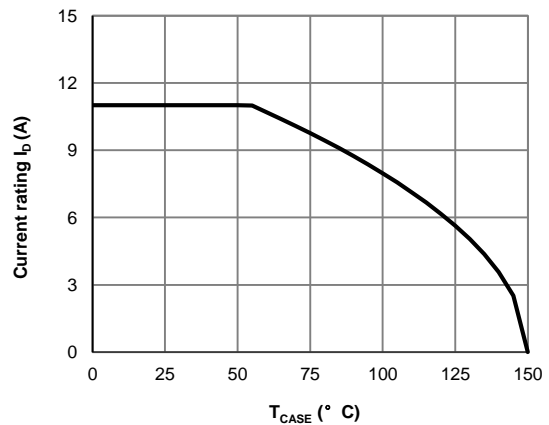


Figure 10: Current De-rating (Note F)

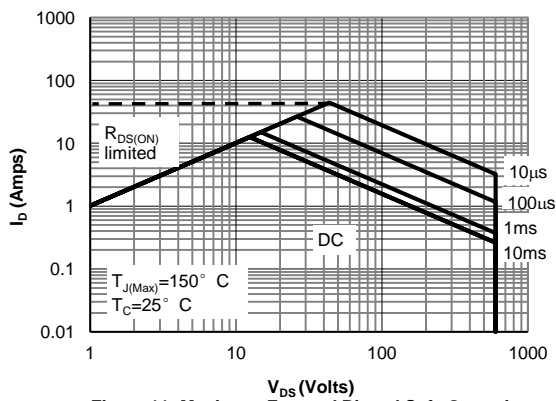


Figure 11: Maximum Forward Biased Safe Operating Area (Note F)

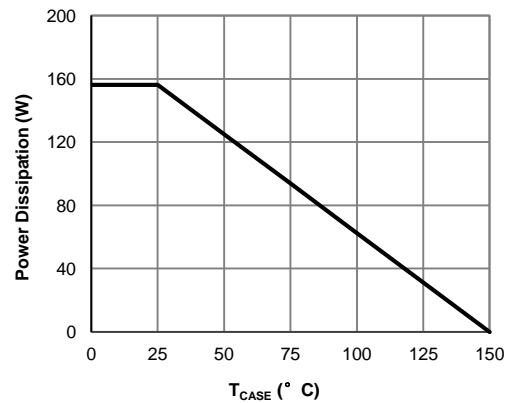


Figure 12: Power De-rating (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

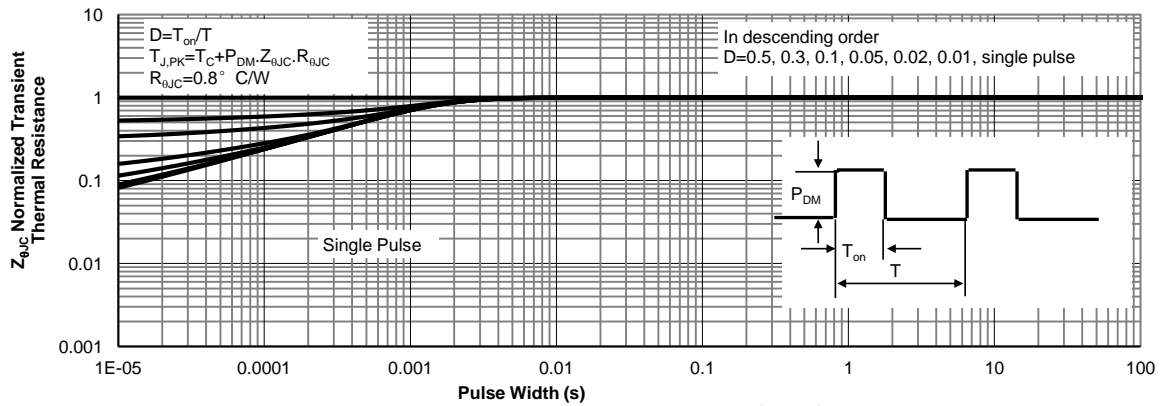


Figure 13: Normalized Maximum Transient Thermal Impedance (Note F)

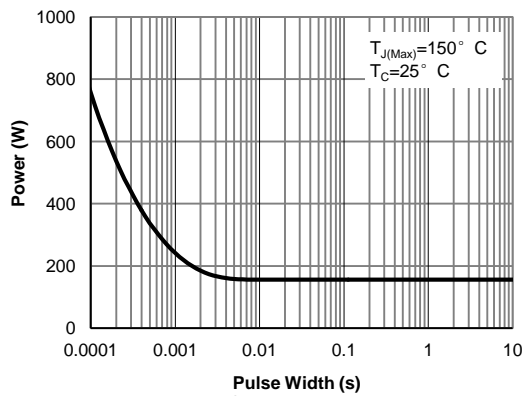


Figure 14: Single Pulse Power Rating Junction-to-Case (Note F)

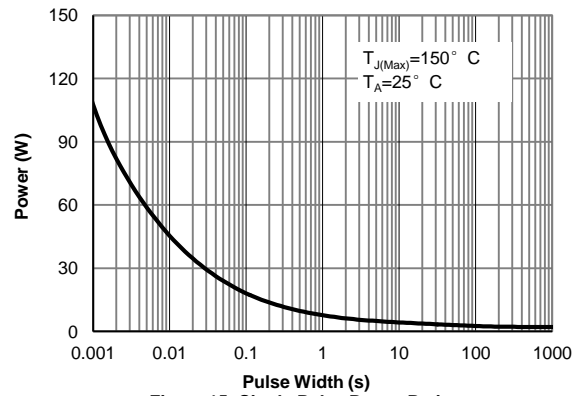


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

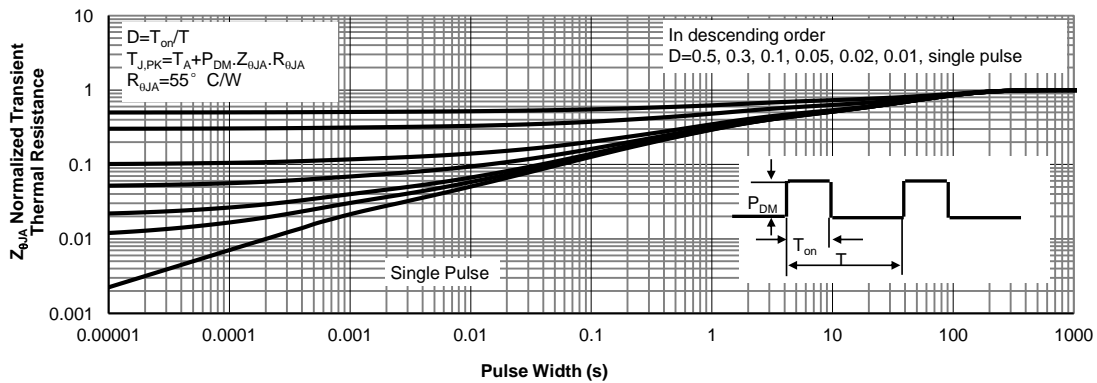
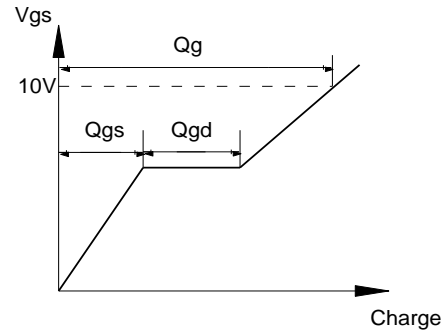
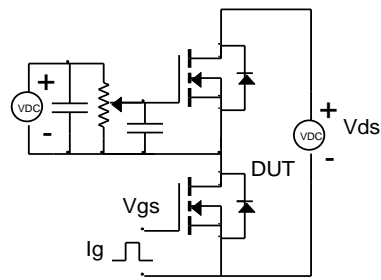
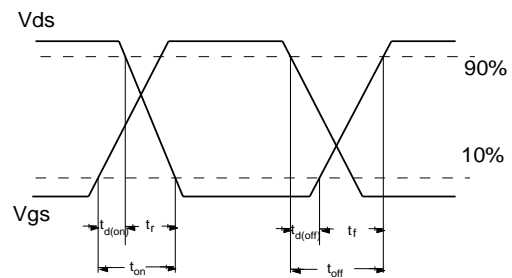
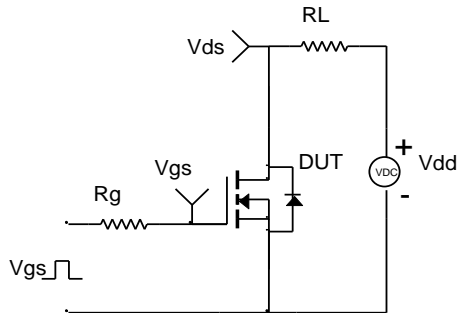


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

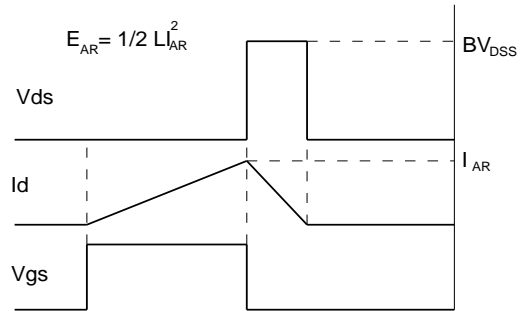
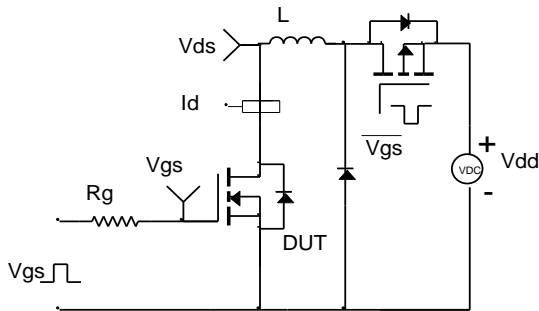
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

